

<b>MoS<sub>2</sub></b>		
<b>Property</b>	<b>Description/Value</b>	
	<b>Bulk</b>	<b>Monolayer</b>
Lattice constant (a)	3.19 Å [1]	3.20 Å [1, 2]
c/a ratio	3.86 [1]	-----
Cohesive energy	4.96 eV/atom [1]	4.98 eV/atom [1]
Dielectric constant ( $\epsilon$ )	8.5 ( $\epsilon_{  }$ ), 13.5 ( $\epsilon_{\perp}$ ) [3]	2.8 ( $\epsilon_{  }$ ), 4.2 ( $\epsilon_{\perp}$ ) [3]
Effective masses	-----	$m_e=1.182 m_o$ , $m_h=3.108m_o$ [3]
Effective Bohr radius	-----	9.3 Å [3]
Band gap type	Indirect	Direct [1-3]
Band gap energy	1.29 eV (experimental), 0.89 eV (calculation) [1, 4]	1.80 eV (experimental), 1.57 eV (calculation) [1, 5]
Group	Transition Metal Dichalcogenide [6]	Transition Metal Dichalcogenide [6]
Crystal structure	hP6, space group P6 <sub>3</sub> /mmc, No 194 (2H)  hR9, space group R3m, No 160 (3R) [7]	hP6, space group P6 <sub>3</sub> /mmc, No 194 (2H)  hR9, space group R3m, No 160 (3R) [7]
Mo-S bond length	2.41 Å [8, 9]	2.41 Å [8, 9]
S-Mo-S bond angle	80.84° [9]	80.88° [9]
Spin-orbit splitting	-----	0.15 eV [8]
Molar mass	160.07 g/mol [10]	160.07 g/mol [10]
Charge transfer of Mo atom	1.09 e [8]	1.09 e [8]
In-plane stiffness	-----	124.24 N/m [8]
Density	5.06 g/cm <sup>3</sup> [10]	5.06 g/cm <sup>3</sup> [10]
Melting point	1,185 °C (decomposes) [10]	-----
Exciton binding energy	-----	1.02 eV [11]
Solubility	decomposed by hot sulfuric acid, aqua regia and nitric acid (insoluble in dilute acids) [10]	decomposed by hot sulfuric acid, aqua regia and nitric acid (insoluble in dilute acids) [10]
Coordination geometry	Trigonal prismatic (Mo), Pyramidal (S) [12]	Trigonal prismatic (Mo), Pyramidal (S) [12]
Thermal conductivity at 300K	-----	34.5±4 W/mK (experimental) [13]
Complex refractive index	-----	Real part $n_i = 4.49$ , imaginary part $k_i= 1.01$ (experimental) [14]
Appearance	Silvery black solid [10]	-----
<b>Carrier mobility in MoS<sub>2</sub> [15, 16]</b>		
<b>Thicknesses</b>	<b>PMMA/SiO<sub>2</sub>/Si substrate</b>	<b>SiO<sub>2</sub>/Si Substrate</b>
1.5 nm	30 cm <sup>2</sup> /V.Sec (electron)	30-60 cm <sup>2</sup> /V.Sec (electron)
6.5 nm	68 cm <sup>2</sup> /V.Sec (electron), 1 cm <sup>2</sup> /V.Sec (hole)	30-60 cm <sup>2</sup> /V.Sec (electron)

47 nm	480 cm <sup>2</sup> /V.Sec (hole), 270 cm <sup>2</sup> /V.Sec (electron)	30-60 cm <sup>2</sup> /V.Sec (electron)
80 nm	250 cm <sup>2</sup> /V.Sec (hole), 50 cm <sup>2</sup> /V.Sec (electron)	30-60 cm <sup>2</sup> /V.Sec (electron)

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